

**AMENDMENTS TO THE CLAIMS:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

**LISTING OF CLAIMS:**

1-7. (Canceled)

8. (Currently amended) A component of semiconductor processing equipment, the component comprising a substrate having a surface and a liquid crystalline polymer coating on the surface of the substrate and forming an outer surface of the component, the outer surface being resistant to plasma erosion and corrosion in the semiconductor processing equipment, wherein the component is a component ~~other than a chamber liner~~ selected from the group consisting of a plasma chamber wall, a gas distribution plate, a gas ring, a pedestal, an electrostatic chuck and a focus ring.

9. (Canceled)

10. (Previously presented) The component according to Claim 8, wherein the substrate comprises aluminum or an aluminum alloy.

11. (Previously presented) The component according to Claim 8, wherein the substrate comprises alumina.

12. (Previously Presented) The component according to Claim 10, wherein the substrate includes an anodized surface.

13. (Previously presented) A component of semiconductor processing equipment, the component comprising a substrate including a surface and a plasma-sprayed liquid crystalline polymer coating on the surface of the substrate and forming an outer surface of the component, the outer surface being resistant to plasma erosion and corrosion in the semiconductor processing equipment.

14. (Canceled)

15. (Previously presented) The component according to Claim 8, wherein the liquid crystalline polymer comprises a preformed sheet covering the surface of the substrate.

16. (Previously Presented) The component according to Claim 13, wherein the component comprises a roughened surface that has been subjected to a surface roughening treatment and is in contact with the plasma sprayed coating applied on the roughened surface.

17. (Original) The component according to Claim 8, wherein the liquid crystalline polymer contains a filler.

18. (Original) A plasma chamber comprising at least one component according to Claim 8.

19-23. (Canceled)

24. (Previously presented) The component according to Claim 13, wherein the component is a plasma chamber wall, a chamber liner, a gas distribution plate, a gas ring, a pedestal, an electrostatic chuck or a focus ring.

25. (Currently amended) A component of semiconductor processing equipment, wherein the component is a component ~~ether than a chamber liner~~ selected from the group consisting of a plasma chamber wall, a gas distribution plate, a gas ring, a pedestal, an electrostatic chuck and a focus ring and comprises a liquid crystalline polymer on an outer surface thereof, the liquid crystalline polymer comprises a coating on a bead or grit-blasted roughened surface of a substrate which is mechanically keyed or interlocked with the coating.

26. (Previously presented) The component according to Claim 8, further comprising at least one intermediate layer between the surface of the substrate and the coating.

27. (Previously presented) The component according to Claim 8, wherein the substrate is of stainless steel, a refractory metal or a polymeric material.

28. (Previously presented) The component according to Claim 8, wherein the substrate is of a ceramic material selected from the group consisting of silicon carbide, silicon nitride, boron carbide and boron nitride.

29. (Previously presented) A component of semiconductor processing equipment, the component comprising a substrate including a bead or grit-blasted roughened surface and a plasma-sprayed liquid crystalline polymer coating on the roughened surface, wherein the roughened surface is mechanically keyed or interlocked with the plasma sprayed coating.

30. (Previously Presented) The component according to Claim 13, further comprising at least one intermediate layer between the surface of the component and the plasma sprayed coating.

31. (Previously Presented) The component according to Claim 13, wherein the substrate is of stainless steel, a refractory metal or a polymeric material.

32. (Previously Presented) The component according to Claim 13, wherein the substrate is of a ceramic material selected from the group consisting of silicon carbide, silicon nitride, boron carbide and boron nitride.

33. (Currently amended) The component according to Claim 8, wherein the component is ~~other than an electrostatic chuck~~ selected from the group

consisting of a plasma chamber wall, a gas distribution plate, a gas ring, a pedestal and a focus ring.

34. (Previously presented) The component according to Claim 8, which consists essentially of the substrate and the plasma-sprayed liquid crystalline polymer coating on the surface of the substrate and forming the outer surface of the component.

35. (Currently amended) The component according to Claim 13, wherein the component is ~~other than an electrostatic chuck~~ selected from the group consisting of a plasma chamber wall, a chamber liner, a gas distribution plate, a gas ring, a pedestal and a focus ring.

36. (Previously presented) The component according to claim 13, which consists essentially of the substrate and the plasma-sprayed liquid crystalline polymer coating on the surface of the substrate and forming the outer surface of the component.